

Previous negative medical experience has significant influence on children's dental anxiety, supporting the Rachmans conditioning theory (Rachman, 1991). Anxious children are more likely to exhibit behaviour problems (aggression) and are more introvert in expressing their judgement regarding the dentist. Both the S - DAI and teh CFSS - DS, which was standardized in the Croatian population sample, showed the highest reliability in assessment of children's dental anxiety.

## Učinak terapijskoga lasera (LLLT) na *Candidu albicans* u dva bolesnika s protetskim stomatitisom

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Protetski stomatitis jedna je od vrlo čestih upala sluznice nepca koja se javlja u nositelja stomatoloških proteza, a povezano s infekcijom gljivicama *Candidom albicans*. Predloženi su različiti terapijski postupci u liječenju protetskoga stomatitisa od kojih ni jedan nije pokazao potpuni ni trajniji terapijski učinak.

Svrha rada bila je ispitati i prikazati učinak terapijskoga lasera na rast gljivice *Candide albicans* i upalu sluznice nepca u dva bolesnika s protetskim stomatitisom.

Dva ispitanika s protetskim stomatitisom kod kojih je dijagnosticirana upala sluznice nepca stupnja II po Newtonu liječeni su niskoenergetskim (terapijskim) poluvodičkim laserom (BTL 2000, Prag, Češka) različitim valnim duljinama (685 nm i 830 nm) tijekom 5 dana uzastopce. Palatalna sluznica i akrilatna baza proteze u oba je bolesnika obasjana terapijskom sondom na udaljenosti od 0,5 cm od površine s različitim vremenom trajanja terapije ovisno o valnoj duljini: tijekom 5 minuta s valnom duljinom 830 nm, (3,0 J/cm<sup>2</sup>, W = 30 mW) i 10 minuta s valnom duljinom 685 nm (3,0 J/cm<sup>2</sup>, W =

30 mW). Prije terapije laserom sa sluznice nepca i proteze uzet je ubrisak za kulturu na *Candidu albicans*. Učinak terapijskog lasera na rast gljivica *in vivo* procijenjen je semikvantitativno po završetku terapije laserom brojem kolonija na agar ploči po Olsenu. Intenzitet upale procijenjen je kliničkim kriterijima.

Nakon terapije laserom zapaženo je da je smanjen broj kolonija na agar pločama, a upale sluznice nije bilo.

Terapijski laser pokazao je dobar klinički učinak u tretmanu protetskoga stomatitisa.

## The Effect of Low Level Laser Therapy on *Candida Albicans* in Patients with Denture Stomatitis - Case Report

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The purpose of this study was to present the effect of low level laser therapy on *Candida albicans* growth and palatal inflammation in two patients with denture stomatitis.

The most common oral mucosal disorder in denture wearers in denture stomatitis, a condition which is usually associated with the presence of the yeast *Candida albicans*. Different treatment methods have been suggested to treat this symptom, none of which is proven to be absolutely effective.

Two denture wearing patients, both with palatal inflammation diagnosed as Newton type II denture stomatitis were treated with low power semiconductor diode laser (BTL-2000, Prague, Czech Republic) with different wavelengths (685 nm and 830 nm) for five days consecutively. In both patients, palatal mucosa and acrylic denture base were irradiated in non-contact mode (probe distance 0.5 cm from irradiated area) with different exposure times, 5 minutes (830 nm, 3.0 J/cm<sup>2</sup>, W = 60 mW) and 10